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Edited by B.J. Pawlak, K.S. Jones, S.B. Felch and M. Hane

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Doping Engineering for Device Fabrication

Symposium held April 18–19, 2006, San Francisco, California, U.S.A.

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PREFACE

This volume contains papers presented at Symposium C, "Sub-Second Rapid Thermal Processing for Device Fabrication," held April 18–19 at the 2006 MRS Spring Meeting in San Francisco, California. The scope of the symposium was to bring together researchers from the field of materials science to review the state-of-the art in doping engineering and activation technologies for integrated circuits, to discuss the current achievements, remaining challenges, and to identify future research directions. These proceedings document the recent developments in the areas of experiments, modeling and metrology related to transistor source and drain regions.

It has been a pleasure and privilege to have the opportunity to organize the symposium and edit this volume. This would not be possible without the support and contributions of the speakers, authors, and sponsors, all of whom are gratefully acknowledged.

Many exciting research achievements have been presented at this symposium. We hope that the readers will enjoy reading this proceedings, and find the contents of the proceedings both informative and interesting.

B.J. Pawlak
K.S. Jones
S.B. Felch
M. Hane

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